

STARPOWER

SEMICONDUCTOR

IGBT

GD150CLU120C2S

1200V/150A chopper in one-package

General Description

STARPOWER IGBT Power Module provides ultra switching speed as well as short circuit ruggedness. They are designed for the applications such as electronic welder and inductive heating.

Features

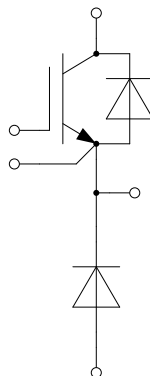
- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Switching mode power supply
- Inductive heating
- Electronic welder

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	219	A
	@ $T_C=75^{\circ}\text{C}$	150	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	300	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	1157	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	150	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	300	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		3.00	3.45	V
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		3.80		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=6.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	3.0	5.0	7.0	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			1.3		Ω
C_{ies}	Input Capacitance			11.0		nF
C_{res}	Reverse Transfer Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.50		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.60		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=6.8\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		71		ns
t_r	Rise Time			52		ns
$t_{d(off)}$	Turn-Off Delay Time			429		ns
t_f	Fall Time			116		ns
E_{on}	Turn-On Switching Loss			9.2		mJ
E_{off}	Turn-Off Switching Loss			7.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=6.8\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		71		ns
t_r	Rise Time			54		ns
$t_{d(off)}$	Turn-Off Delay Time			456		ns
t_f	Fall Time			134		ns
E_{on}	Turn-On Switching Loss			13.2		mJ
E_{off}	Turn-Off Switching Loss			8.3		mJ
I_{SC}	SC Data	$t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		950		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.80	2.25	V
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.75		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=2000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		9.1		μC
I_{RM}	Peak Reverse Recovery Current			153		A
E_{rec}	Reverse Recovery Energy			3.2		mJ
Q_r	Recovered Charge			20.0		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=2000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		191		A
E_{rec}	Reverse Recovery Energy			7.5		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.108	K/W
	Junction-to-Case (per Diode)			0.200	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.021		K/W
	Case-to-Heatsink (per Diode)		0.039		
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

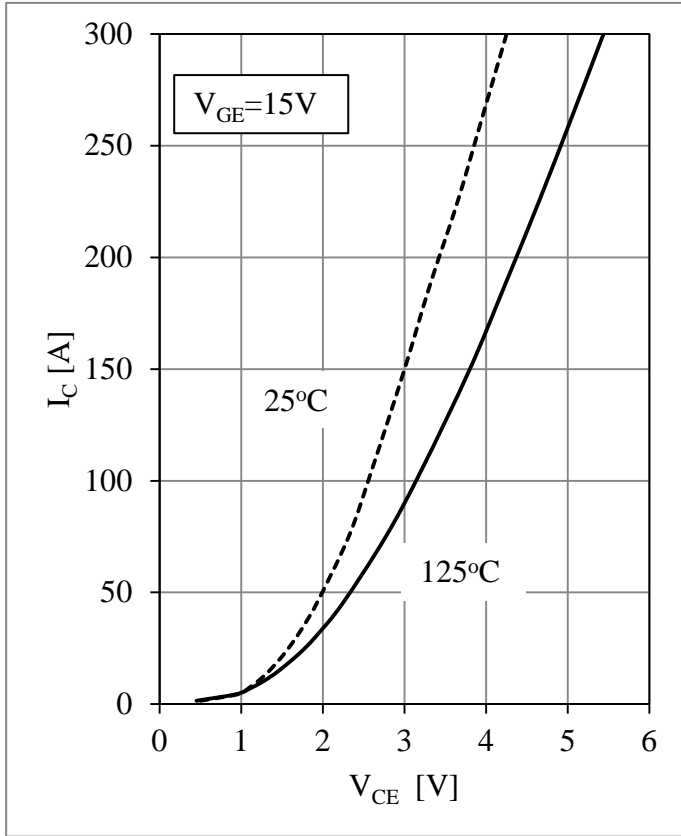


Fig 1. IGBT Output Characteristics

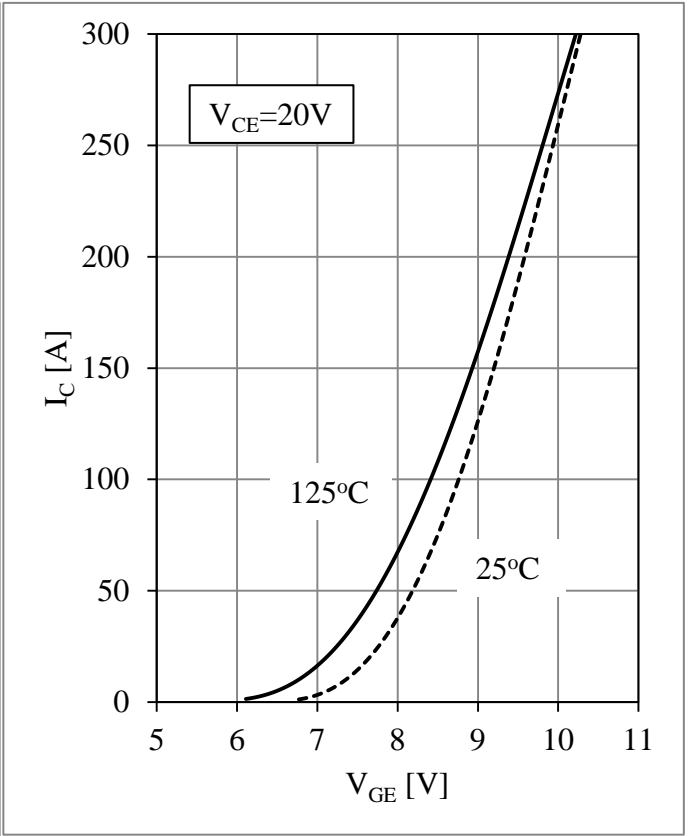


Fig 2. IGBT Transfer Characteristics

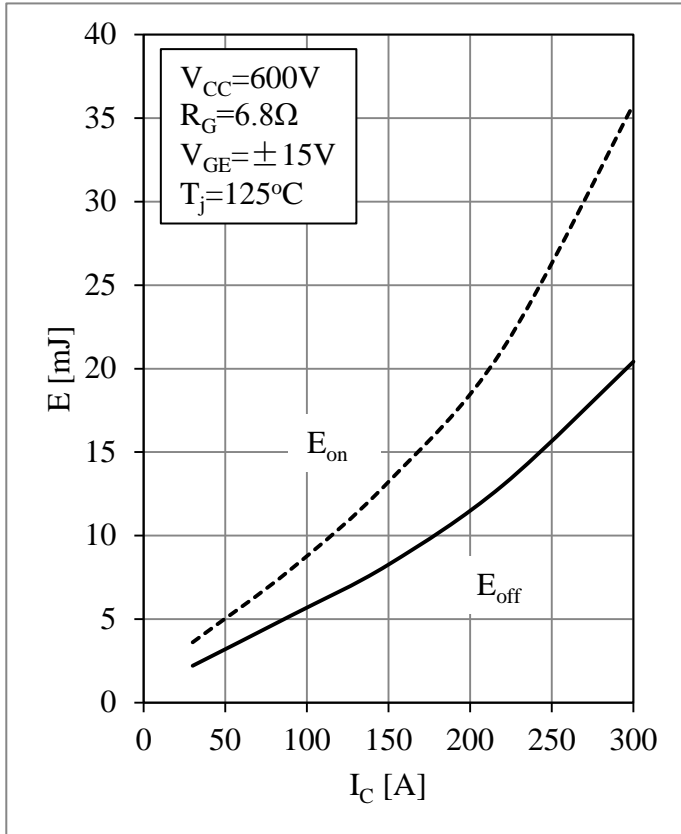


Fig 3. IGBT Switching Loss vs. I_C

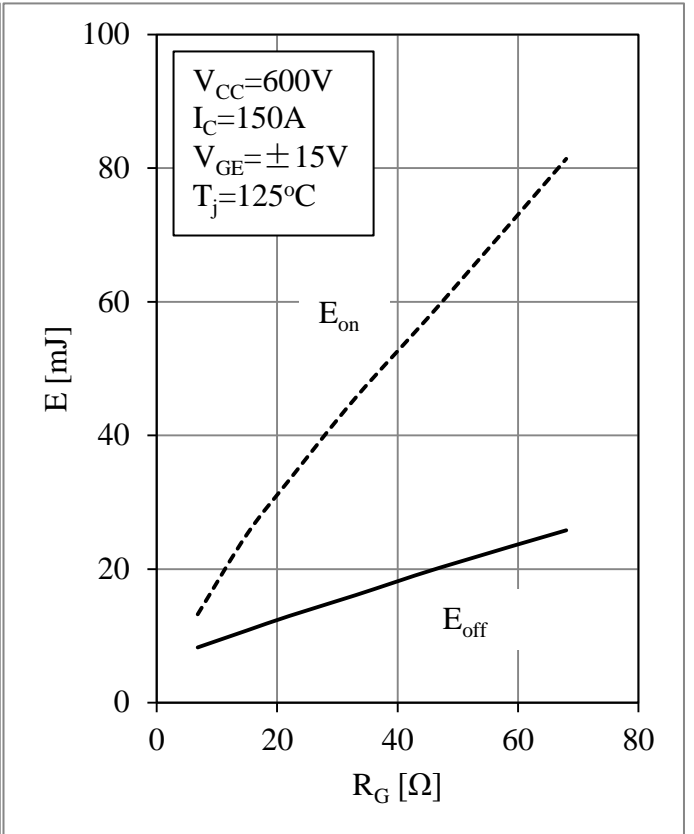


Fig 4. IGBT Switching Loss vs. R_G

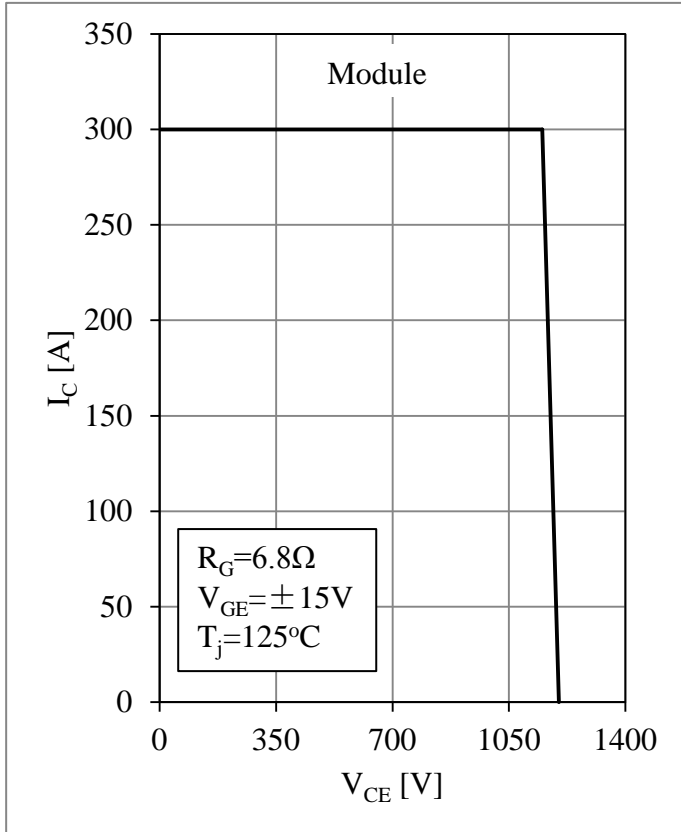


Fig 5. RBSOA

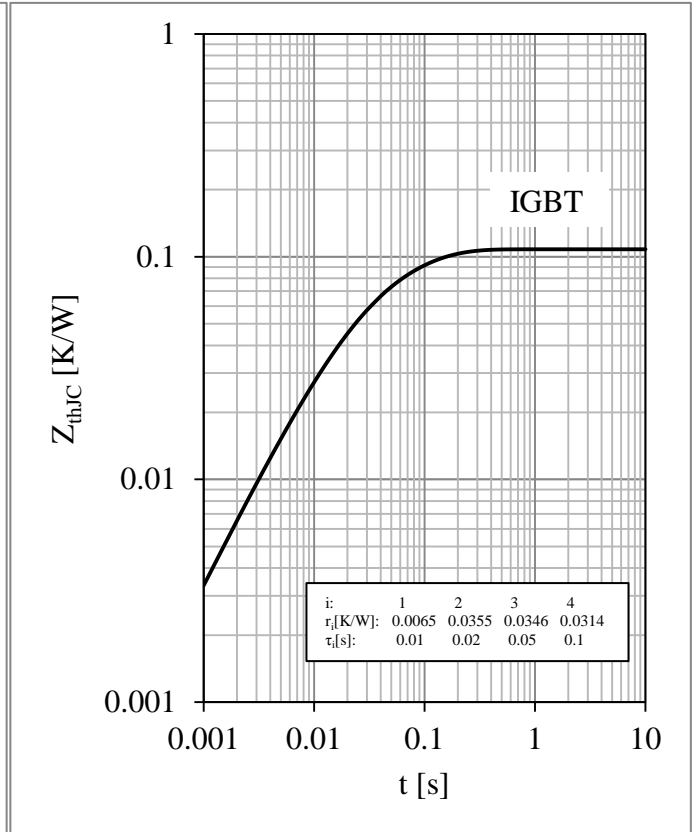


Fig 6. IGBT Transient Thermal Impedance

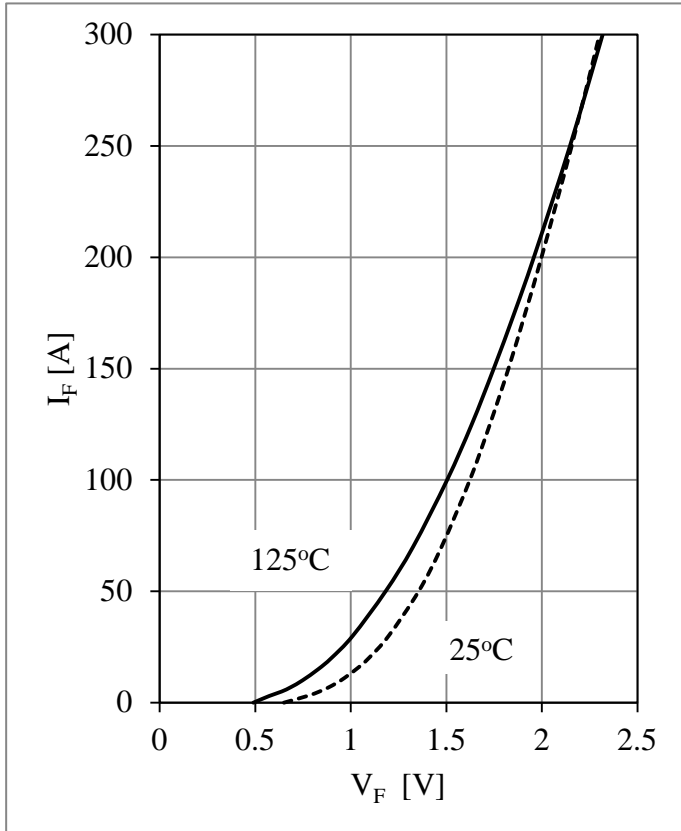


Fig 7. Diode Forward Characteristics

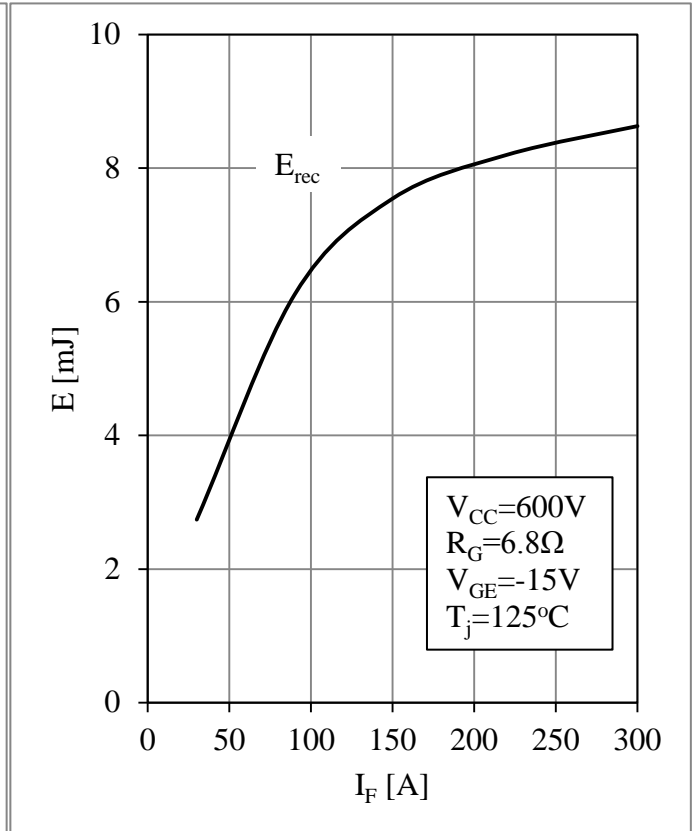


Fig 8. Diode Switching Loss vs. I_F

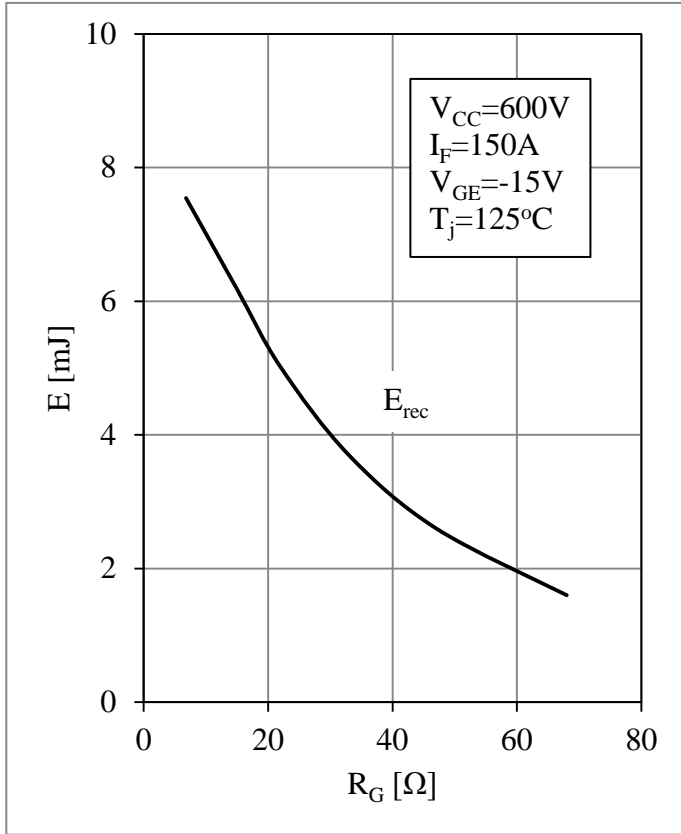


Fig 9. Diode Switching Loss vs. R_G

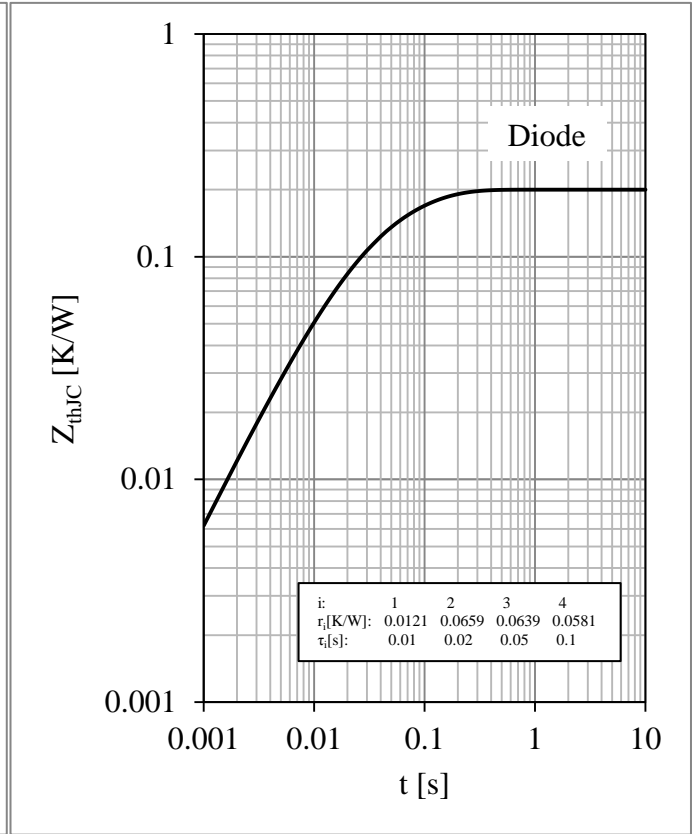
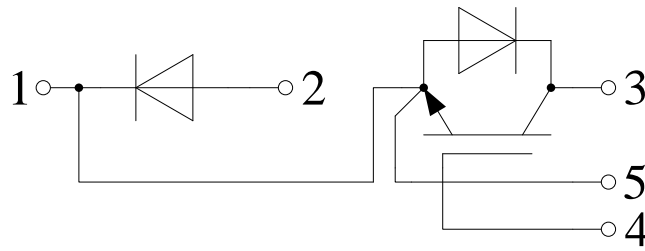


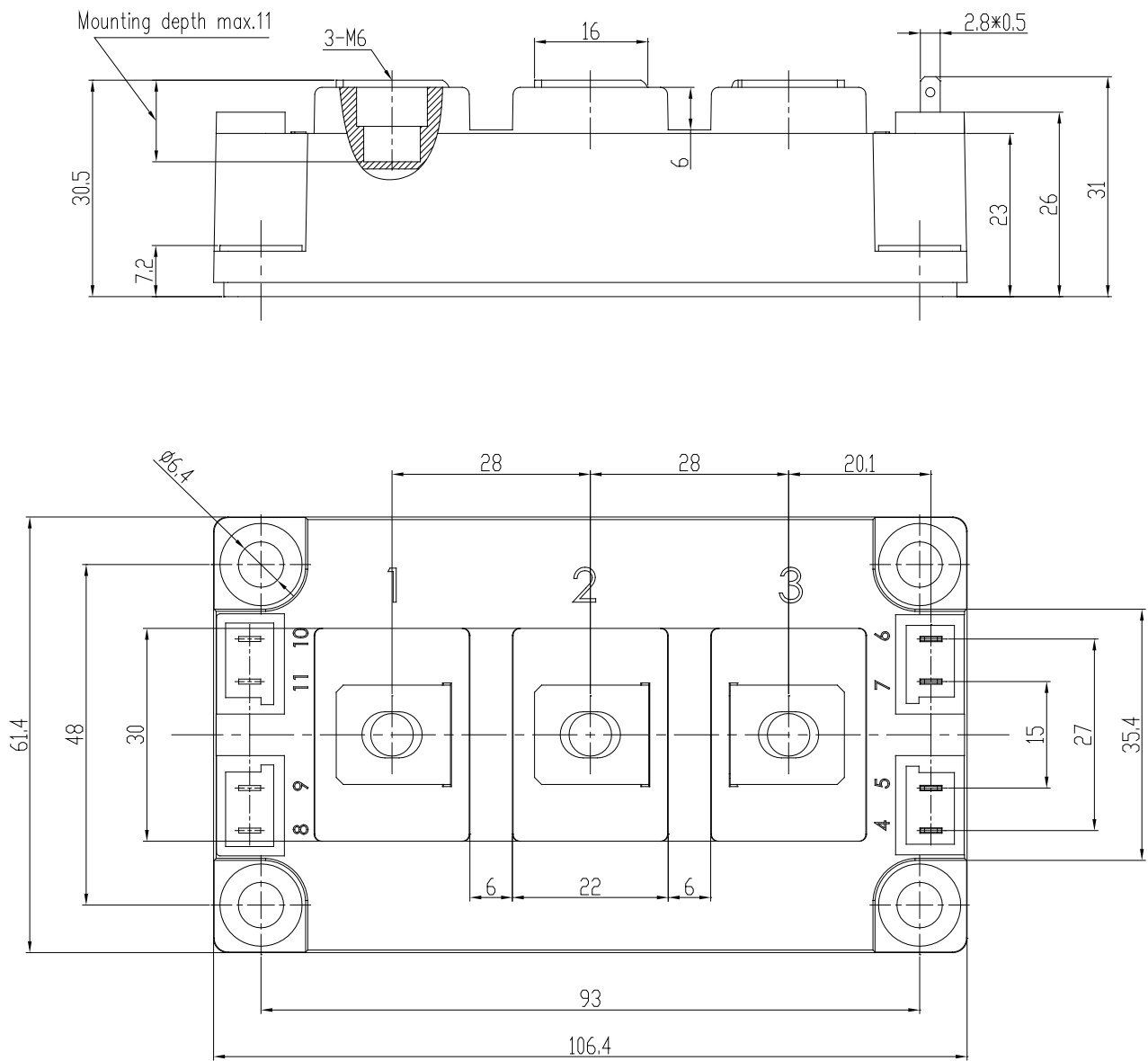
Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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